

FABRICATION OF TEMPERATURE MONITORING SYSTEM FOR ART CONSERVATION

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Introduction

- Currently, monitoring an artwork's temperature requires obtrusive, expensive equipment.
- Being able to produce low cost temperature monitoring systems is imperative for preserving art in all tiers of museums [1].
- Resistance temperature detectors (RTDs) have a linear resistance-temperature relationship [2].
- **Aim:** Create a RTD-based system that can wirelessly monitor artwork's temperature.

Objective

- Design and fabricate a resistance temperature detector (RTD) with a standardized reference resistance.

Materials

- AZ400K
- HMDS
- AZP4110
- Buffer Oxide Etchant (BOE)
- Deionized Water
- Acetone
- Cr_7^+
- FeCl_3
- Glass or Silicon Substrate

Procedures

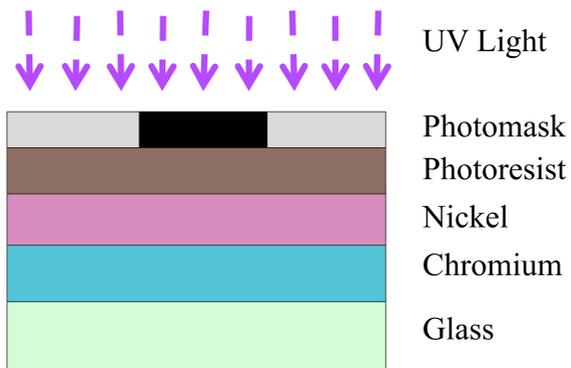
1. Spin coat a layer of HMDS onto wafer.
2. Spin coat a layer of AZP4110 onto wafer.
3. Apply UV light to react photoresist with light.
4. Develop photoresist into photomask pattern.
5. Etch away excess nickel and excess chromium.

References

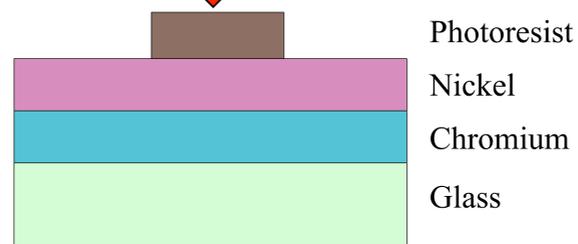
- [1] <https://www.si.edu/mci/downloads/reports/Mecklenburg-Part2-Temp.pdf>
- [2] <http://www.smartsensors.com/specrtds.pdf>

Photolithography

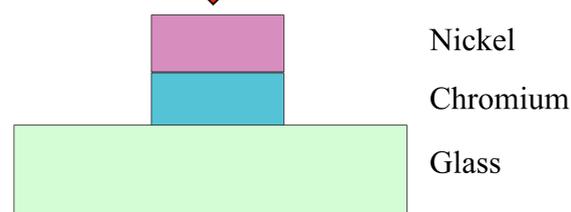
- Process of exposing photoresist to UV light to etch patterns onto a substrate.
- Used to fabricate RTD and signal conditioning circuit.



- UV light etches away photoresist.



- Excess photoresist, nickel, and chromium etched away.



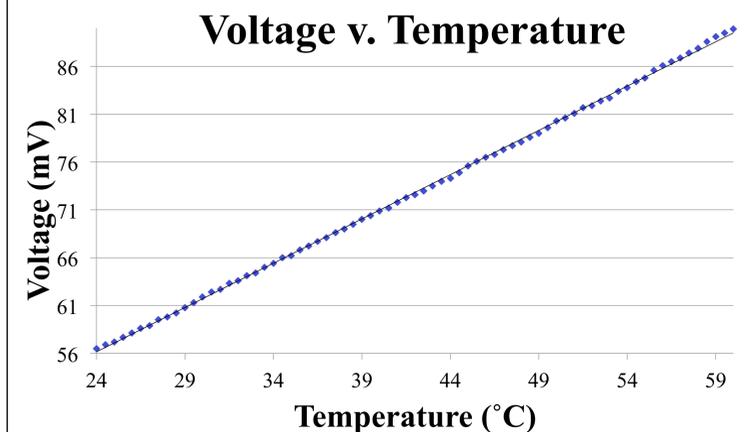
Design

- **Parameters:**
 - Wire thickness = 200 nm.
 - Minimum line width = 200 μm .
 - Spacing between wires = 200 μm .
 - Minimum pad size = 25 \times 25 mm = 625 mm².
- **Calculating Wire Length:**
 - R = Reference Resistance = 100 Ω at 20 $^\circ\text{C}$.
 - ρ = Resistivity = $1.2 \times 10^{-7} \Omega \cdot \text{m}$.
 - A = Cross-sectional area of wire.
= thickness \times width = 40 μm^2 .
 - $R = \frac{\rho L}{A} \rightarrow 100 = \frac{(1.2 \times 10^{-7})L}{40 \times 10^{-12}} \rightarrow L = 3.33 \text{ cm}$.
- **Sample Designs:**



Characterization

- Given the linearity of the temperature-resistance relationship with RTDs, it is possible to characterize a linear equation relating them.
- **Water Bath Testing:**
 - Coated RTD with liquid electrical tape, allowing submersion into water.
 - Measured voltage across RTD in 0.5 $^\circ\text{C}$ increments.
 - Can determine resistance given voltage and constant current source.
- **Results:**
 - $V = 0.9263T + 33.926$
 - V = Voltage (mV)
 - T = Temperature ($^\circ\text{C}$)
 - $R^2 = 0.9996$
 - Extremely linear relationship



Next Steps

- **Short Term:**
 - Characterize newly fabricated RTDs with reference resistance of 100 Ω .
 - Utilize a more precise temperature control system and temperature monitoring system.
- **Long Term:**
 - Integrate a RTD and other sensor into system that can measure an artwork's environment temperature and wirelessly transmit data to a central hub.

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